

Inverter Grade Thyristors (PUK Version), 620 A


E-PUK (TO-200AB)
FEATURES

- Metal case with ceramic insulator
- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- International standard case E-PUK (TO-200AB)
- High surge current capability
- Low thermal impedance
- High speed performance
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

PRIMARY CHARACTERISTICS	
Package	E-PUK (TO-200AB)
Circuit configuration	Single SCR
$I_{T(AV)}$	620 A
V_{DRM}/V_{RRM}	400 V, 800 V, 1000 V, 1200 V
V_{TM}	2.16 V
I_{TSM} at 50 Hz	7950 A
I_{TSM} at 60 Hz	8320 A
I_{GT}	200 mA
T_C/T_{hs}	55 °C

TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		620	A
	T_{hs}	55	°C
$I_{T(RMS)}$		1180	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	7950	A
	60 Hz	8320	
I^2t	50 Hz	316	kA ² s
	60 Hz	289	
V_{DRM}/V_{RRM}		400 to 1200	V
t_q	Range	10 to 30	µs
T_J		-40 to 125	°C

Note

- t_q = 10 µs to 20 µs for 400 V to 800 V devices
- t_q = 15 µs to 30 µs for 1000 V to 1200 V devices

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST303C..C	04	400	500	50
	08	800	900	
	10	1000	1100	
	12	1200	1300	



CURRENT CARRYING CAPABILITY							
FREQUENCY							UNITS
50 Hz	1314	1130	2070	1940	6930	6270	A
400 Hz	1260	1040	2190	1880	3440	2960	
1000 Hz	900	700	1900	1590	1850	1540	
2500 Hz	340	230	910	710	740	560	
Recovery voltage V_r	50		50		50		V
Voltage before turn-on V_d	V_{DRM}		V_{DRM}		V_{DRM}		
Rise of on-state current di/dt	50		-		-		A/μs
Heatsink temperature	40	55	40	55	40	55	°C
Equivalent values for RC circuit	10/0.47		10/0.47		10/0.47		Ω/μF

ON-STATE CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave double side (single side) cooled		620 (230)	A
				55 (85)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled		1180	
Maximum peak, one half cycle, non-repetitive surge current	I_{TSM}	Sinusoidal half wave, initial $T_J = T_J$ maximum	t = 10 ms, No voltage reapplied	7950	A
			t = 8.3 ms, No voltage reapplied	8320	
			t = 10 ms, 100 % V_{RRM} reapplied	6690	
			t = 8.3 ms, 100 % V_{RRM} reapplied	7000	
Maximum I^2t for fusing	I^2t	Sinusoidal half wave, initial $T_J = T_J$ maximum	t = 10 ms, No voltage reapplied	316	kA ² s
			t = 8.3 ms, No voltage reapplied	289	
			t = 10 ms, 100 % V_{RRM} reapplied	224	
			t = 8.3 ms, 100 % V_{RRM} reapplied	204	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied		3160	kIA ² /√s
Maximum peak on-state voltage	V_{TM}	$I_{TM} = 1255$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse		2.16	V
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		1.44	
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		1.48	
Low level value of forward slope resistance	r_{11}	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		0.57	mΩ
High level value of forward slope resistance	r_{12}	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		0.56	
Maximum holding current	I_H	$T_J = 25$ °C, $I_T > 30$ A		600	mA
Typical latching current	I_L	$T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω, $I_G = 1$ A		1000	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned on current	di/dt	$T_J = T_J$ maximum, $V_{DRM} = \text{Rated } V_{DRM}$ $I_{TM} = 2 \times di/dt$		1000	A/μs
Typical delay time	t_d	$T_J = 25$ °C, $V_{DM} = \text{Rated } V_{DRM}$, $I_{TM} = 50$ A DC, $t_p = 1$ μs Resistive load, gate pulse: 10 V, 5 Ω source		0.83	μs
Maximum turn-off time ⁽¹⁾	minimum	$T_J = T_J$ maximum, $I_{TM} = 550$ A, commutating $di/dt = 40$ A/μs $V_R = 50$ V, $t_p = 500$ μs, dV/dt : see table in device code		10	
	maximum			30	

Note

⁽¹⁾ $t_q = 10$ μs to 20 μs for 400 V to 800 V devices; $t_q = 15$ μs to 30 μs for 1000 V to 1200 V devices



BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum, linear to 80 % V _{DRM} , higher value available on request	500	V/μs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	T _J = T _J maximum, rated V _{DRM} /V _{RRM} applied	50	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	T _J = T _J maximum, f = 50 Hz, d% = 50	60	W
Maximum average gate power	P _{G(AV)}		10	
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum, t _p ≤ 5 ms	10	A
Maximum peak positive gate voltage	+ V _{GM}		20	V
Maximum peak negative gate voltage	- V _{GM}		5	
Maximum DC gate current required to trigger	I _{GT}	T _J = 25 °C, V _A = 12 V, R _a = 6 Ω	200	mA
Maximum DC gate voltage required to trigger	V _{GT}		3	V
Maximum DC gate current not to trigger	I _{GD}	T _J = T _J maximum, rated V _{DRM} applied	20	mA
Maximum DC gate voltage not to trigger	V _{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T _J		-40 to 125	°C
Maximum storage temperature range	T _{Stg}		-40 to 150	
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation single side cooled	0.09	K/W
		DC operation double side cooled	0.04	
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation single side cooled	0.020	
		DC operation double side cooled	0.010	
Mounting force, ± 10 %			9800 (1000)	N (kg)
Approximate weight			83	g
Case style		See dimensions - link at the end of datasheet	E-PUK (TO-200AB)	

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.010	0.010	0.007	0.007	T _J = T _J max.	K/W
120°	0.012	0.012	0.012	0.013		
90°	0.015	0.015	0.016	0.017		
60°	0.022	0.022	0.023	0.023		
30°	0.036	0.036	0.036	0.037		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

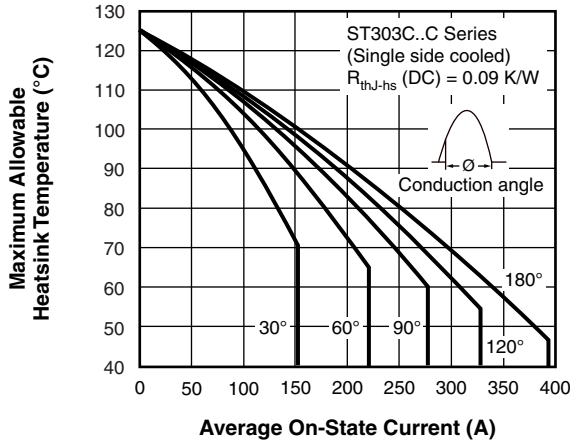


Fig. 1 - Current Ratings Characteristics

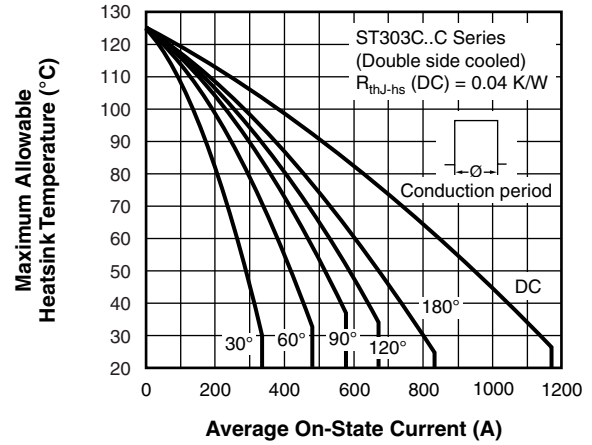


Fig. 4 - Current Ratings Characteristics

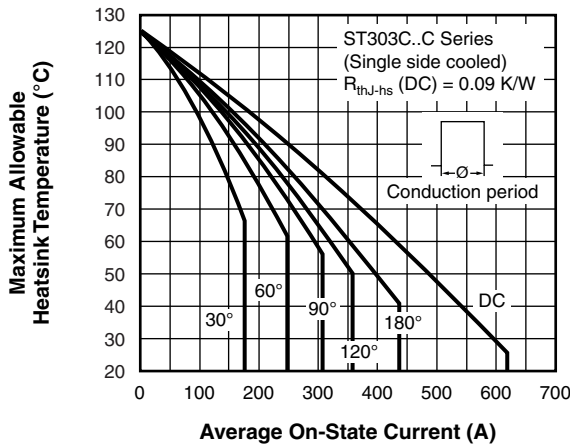


Fig. 2 - Current Ratings Characteristics

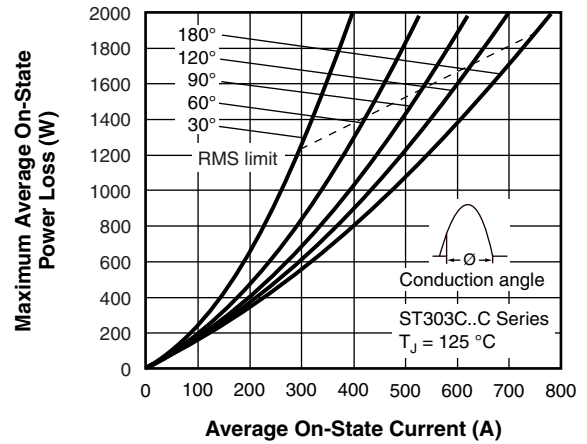


Fig. 5 - On-State Power Loss Characteristics

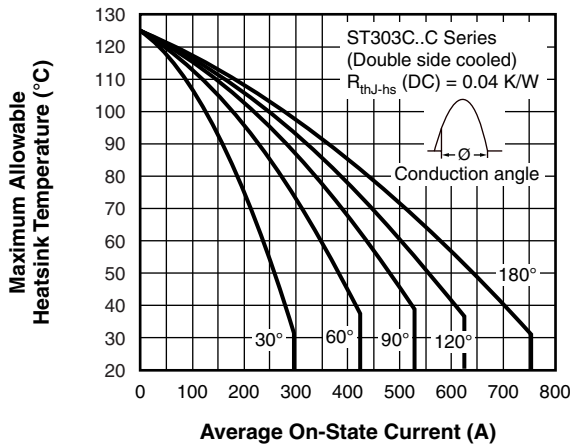


Fig. 3 - Current Ratings Characteristics

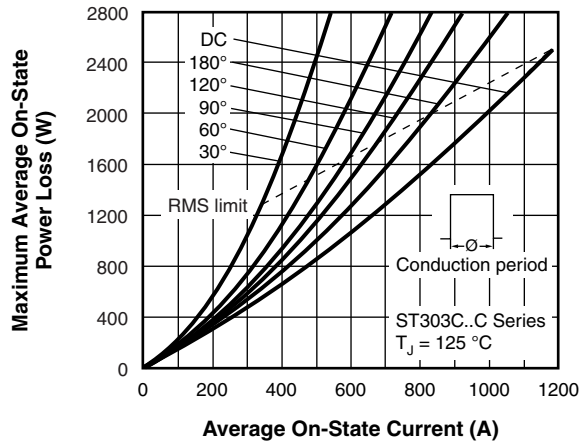


Fig. 6 - On-State Power Loss Characteristics

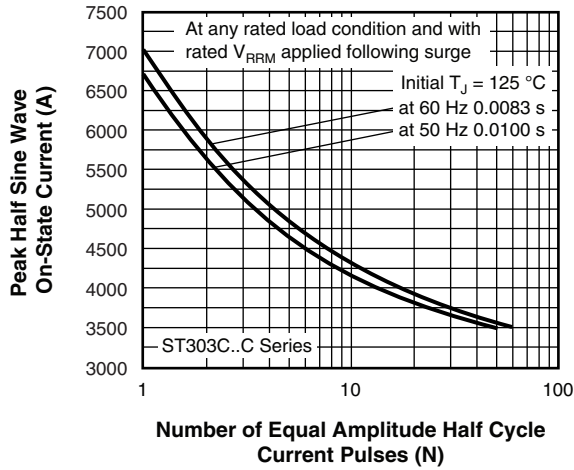


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

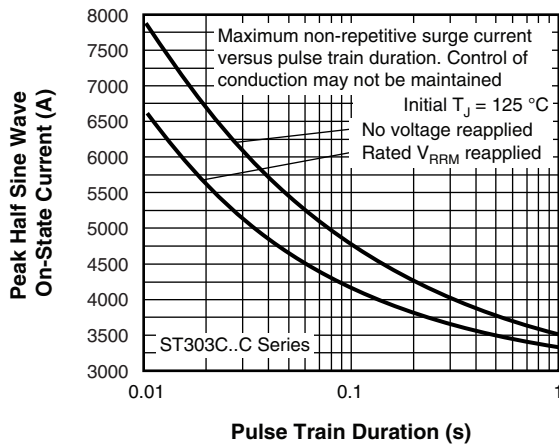


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

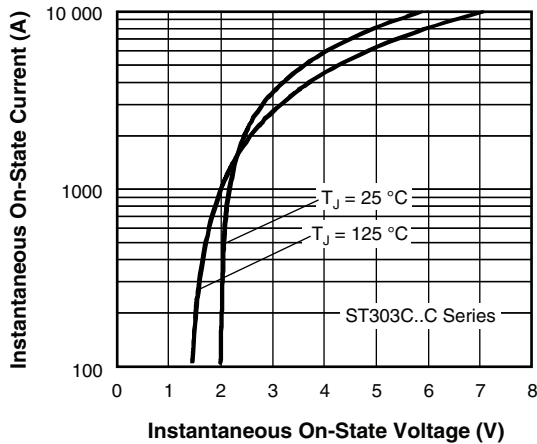


Fig. 9 - On-State Voltage Drop Characteristics

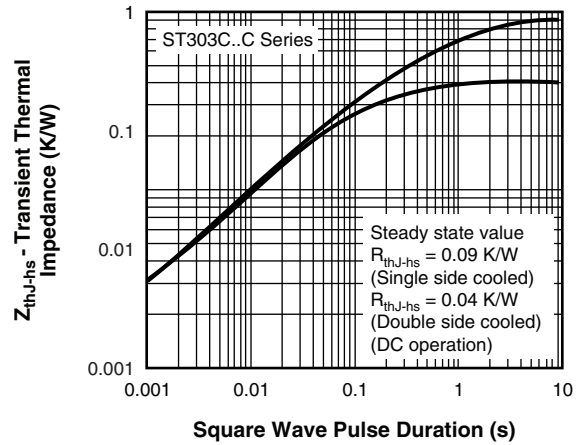


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

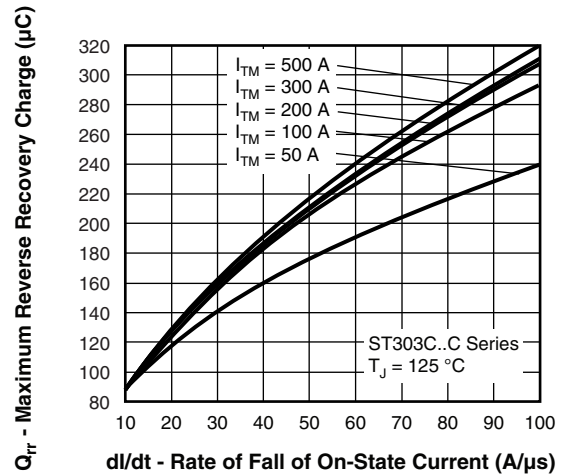


Fig. 11 - Reverse Recovered Charge Characteristics

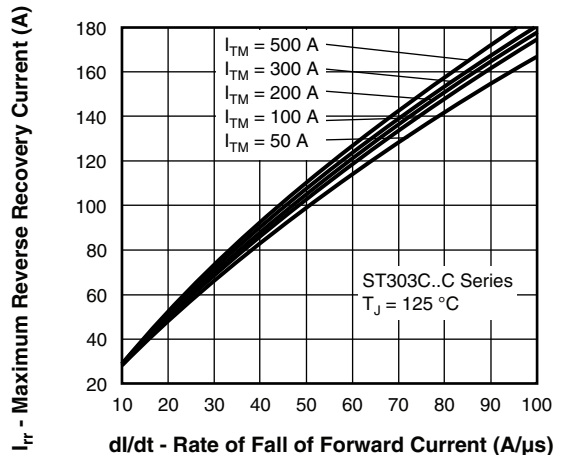


Fig. 12 - Reverse Recovered Current Characteristics

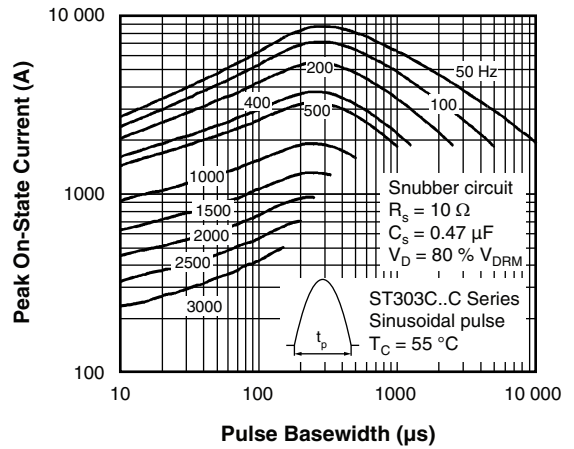
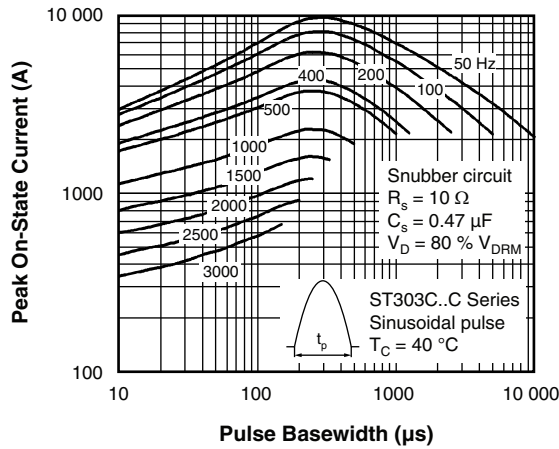


Fig. 13 - Frequency Characteristics

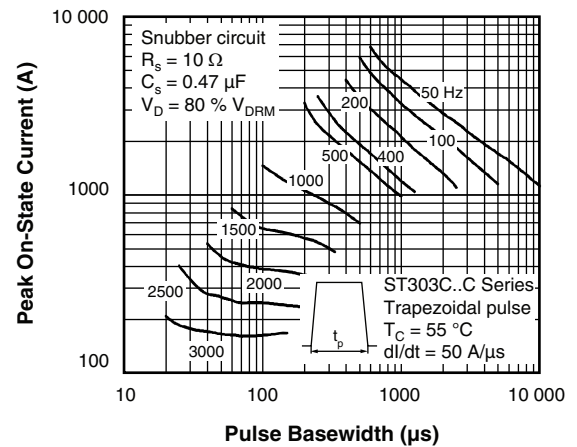
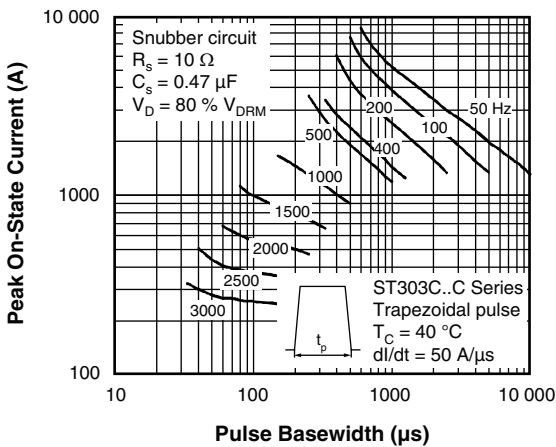


Fig. 14 - Frequency Characteristics

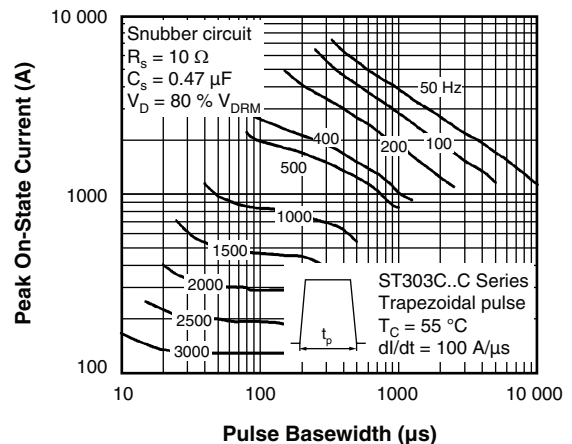
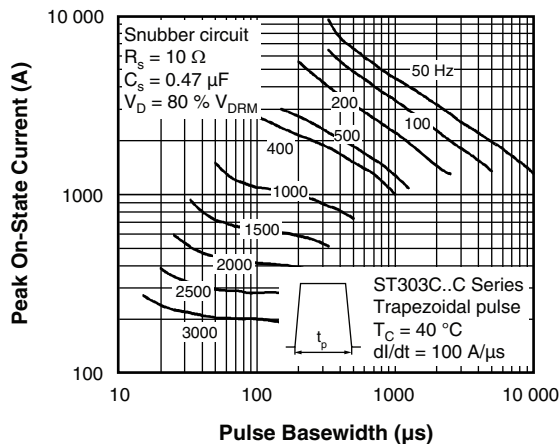


Fig. 15 - Frequency Characteristics

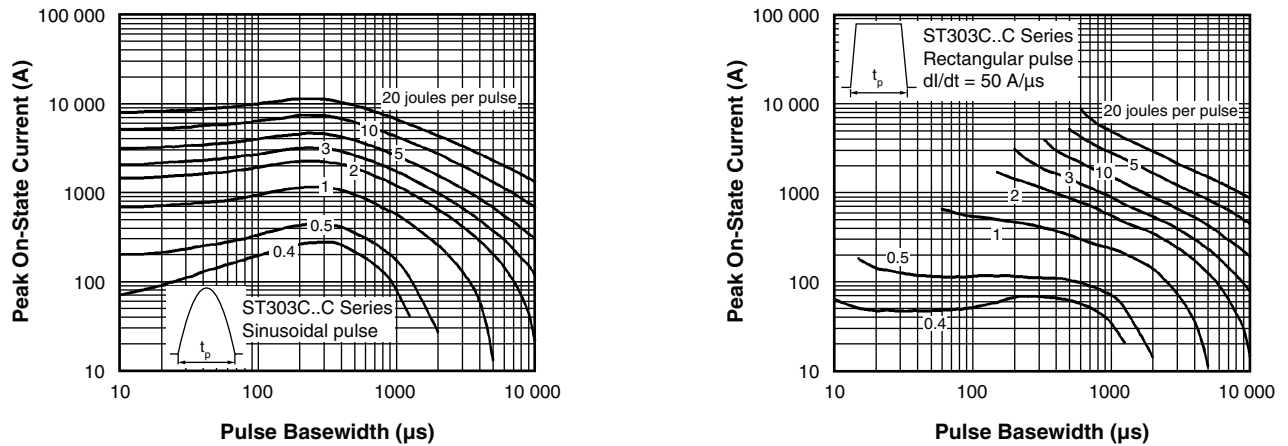


Fig. 16 - Maximum On-State Energy Power Loss Characteristics

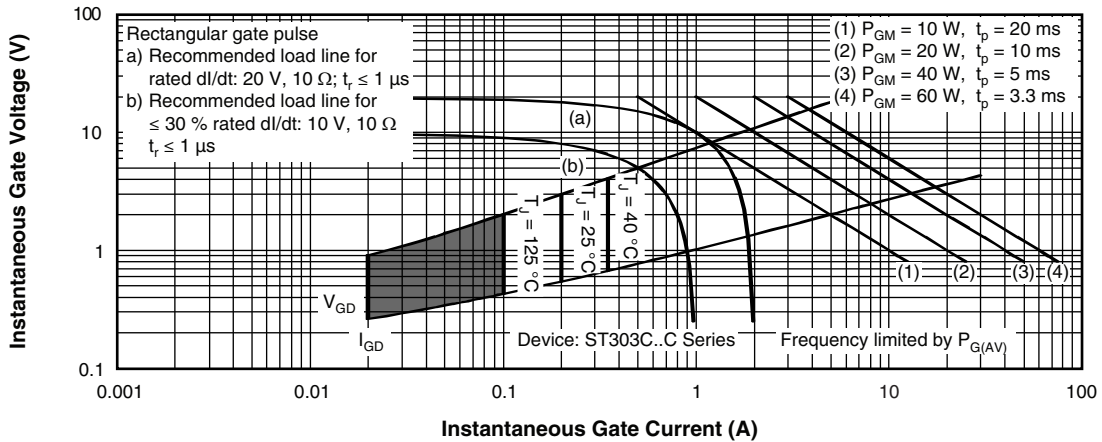


Fig. 17 - Gate Characteristics



ORDERING INFORMATION TABLE

Device code	VS-	ST	30	3	C	12	C	H	K	1	-
	1	2	3	4	5	6	7	8	9	10	11

- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 3 = fast turn-off
- 5** - C = ceramic PUK
- 6** - Voltage code x 100 = V_{RRM}
(see Voltage Ratings table)
- 7** - C = PUK case E-PUK (TO-200AB)
- 8** - Reapplied dV/dt code (for t_q test condition)
- 9** - t_q code
- 10** - 0 = eyelet terminals
(gate and aux. cathode unsoldered leads)
1 = fast-on terminals
(gate and aux. cathode unsoldered leads)
2 = eyelet terminals
(gate and aux. cathode soldered leads)
3 = fast-on terminals
(gate and aux. cathode soldered leads)
- 11** - Critical dV/dt:
 - None = 500 V/ μ s (standard value)
 - L = 1000 V/ μ s (special selection)

		dV/dt - t_q combinations available					
		dV/dt (V/ μ s)	20	50	100	200	400
t_q (μ s) up to 800 V	10	CN	DN	EN	FN*	HN	
	12	CM	DM	EM	FM	HM	
	15	CL	DL	EL	FL*	HL	
	20	CK	DK	EK	FK*	HK	
t_q (μ s)	15	CL	-	-	-	-	
	18	CP	DP	-	-	-	
only for 1000 V/1200 V	20	CK	DK	EK	FK*	HK	
	25	CJ	DJ	EJ	FJ*	HJ	
	30	-	DH	EH	FH	HH	

* Standard part number.
All other types available only on request.

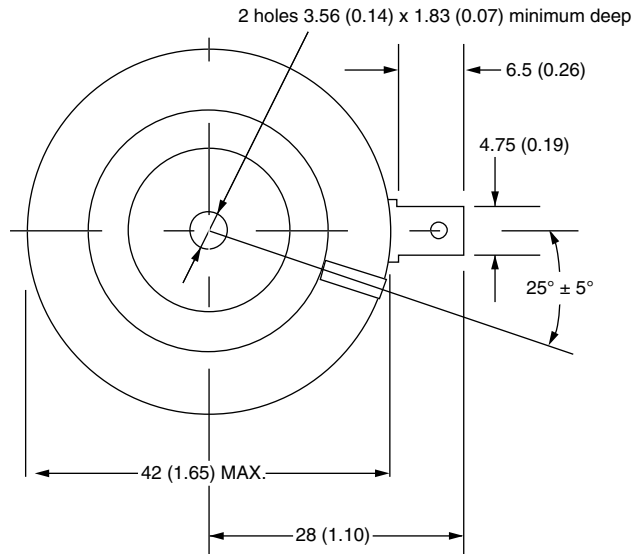
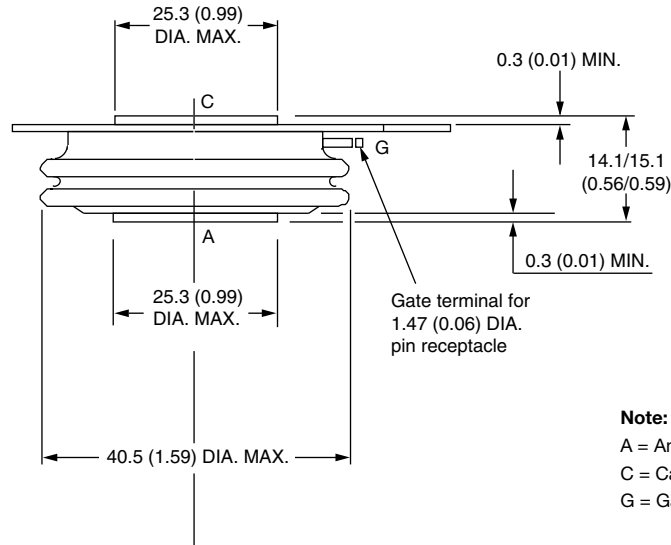
LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95075



E-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate
Creepage distance: 11.18 (0.44) minimum
Strike distance: 7.62 (0.30) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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